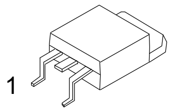
UTC **UNISONIC TECHNOLOGIES CO., LTD**

2A, 650V N-CHANNEL POWER MOSFET



TO-252

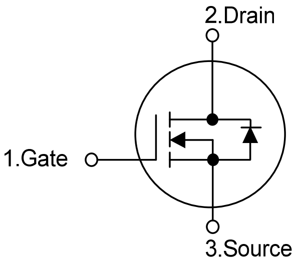
■ DESCRIPTION

The UTC **2N65-TD** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

■ FEATURES

* $R_{DS(ON)} \leq 5.0\ \Omega$ @ V_{GS}=10V, I_D=1.0A
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness

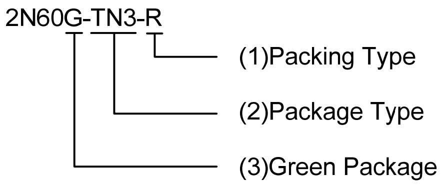
■ SYMBOL



■ ORDERING INFORMATION

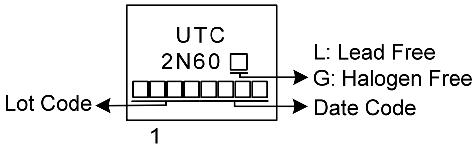
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N65L-TN3-R	2N65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) R: Tape Reel
(2) TN3: TO-252
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current		I_D	2	A
Pulsed Drain Current (Note 2)		I_{DM}	4	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	108.3	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4	V/ns
Power Dissipation		P_D	44.5	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 30mH, I_{AS} = 2.6A, V_{DD} = 80V, R_G = 25 Ω, Starting T_J = 25°C
4. I_{SD} ≤ 2.0A, di/dt ≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	2.8 (Note)	°C/W

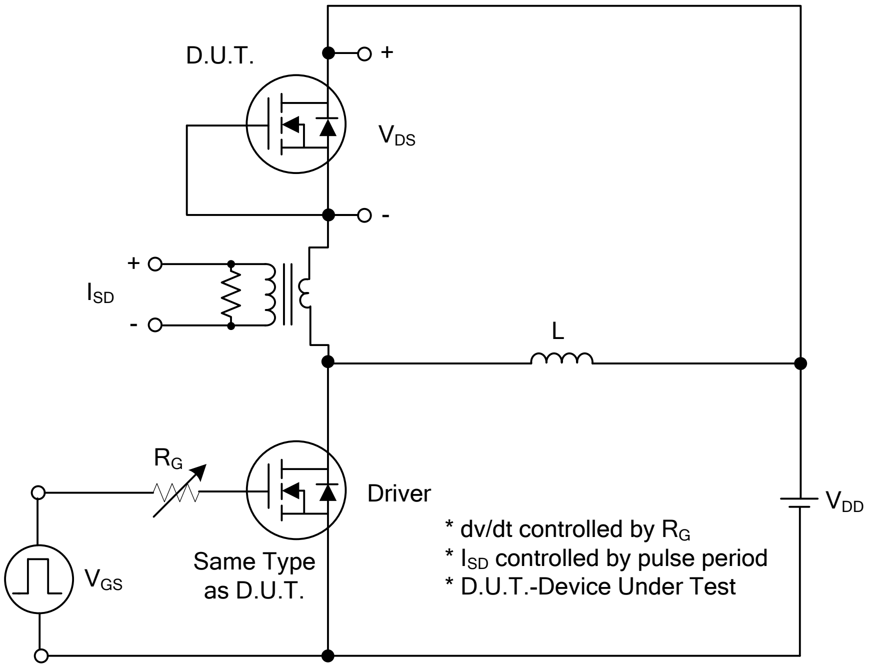
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

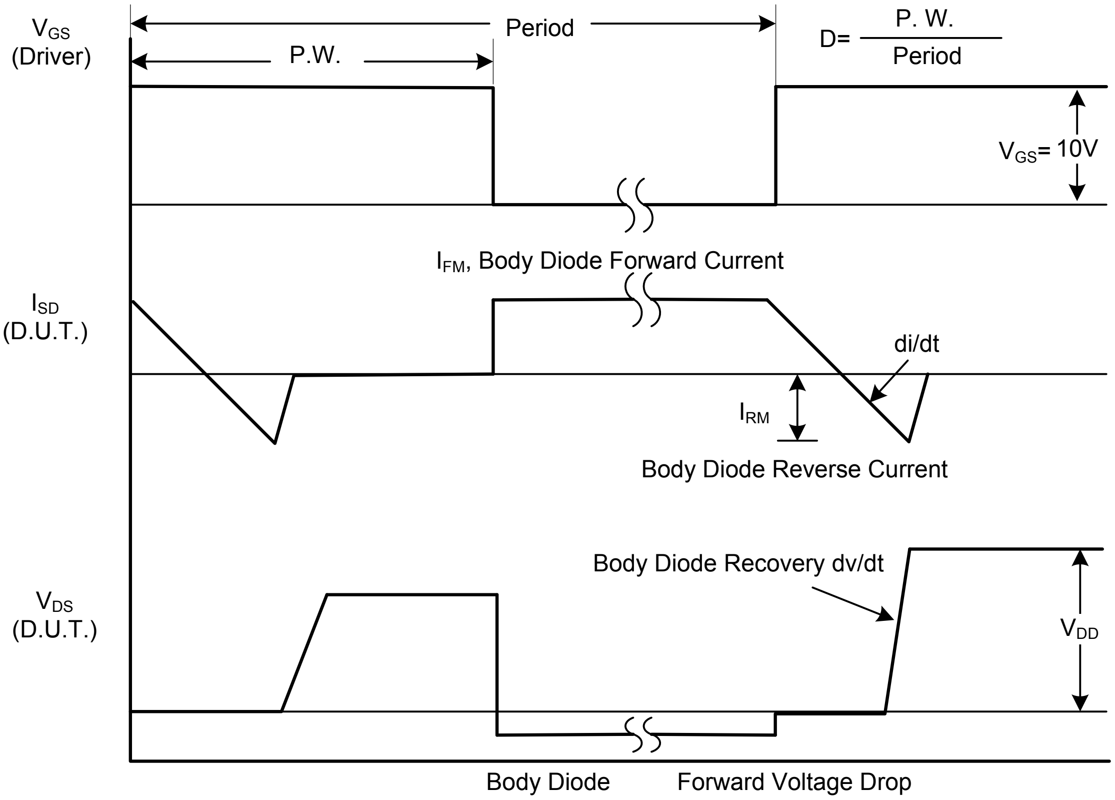
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0V, I_D = 250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 650V, V_{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30V, V_{DS} = 0V			100	nA
	Reverse		V_{GS} = -30V, V_{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10V, I_D = 1.0A			5.0	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1.0 MHz		234.1		pF
Output Capacitance		C_{OSS}			30.8		pF
Reverse Transfer Capacitance		C_{RSS}			2.7		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=520V, V_{GS}=10V, I_D=2.0A, I_D=1mA (Note 1, 2)		11.3		nC
Gate-Source Charge		Q_{GS}			4.2		nC
Gate-Drain Charge		Q_{GD}			1.9		nC
Turn-On Delay Time (Note 1)		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D =2.0A, R_G =25Ω (Note 1, 2)		6.7		ns
Turn-On Rise Time		t_R			15.7		ns
Turn-Off Delay Time		$t_{D(OFF)}$			24.4		ns
Turn-Off Fall Time		t_F			28.7		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Maximum Body-Diode Continuous Current		I_S				2	A
Maximum Body-Diode Pulsed Current		I_{SM}				4	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=2.0A , V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=2.0A , V_{GS}=0V di/dt=100A/μs		193.3		ns
Body Diode Reverse Recovery Charge		Q_{rr}			1.7		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

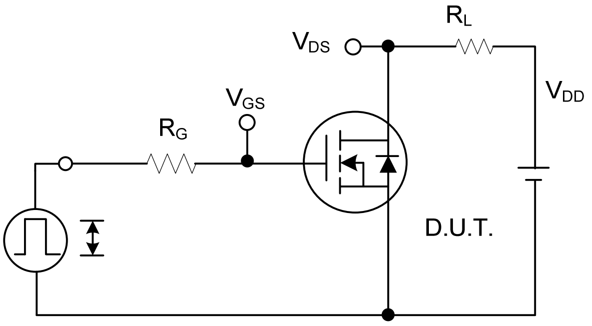


Peak Diode Recovery dv/dt Test Circuit

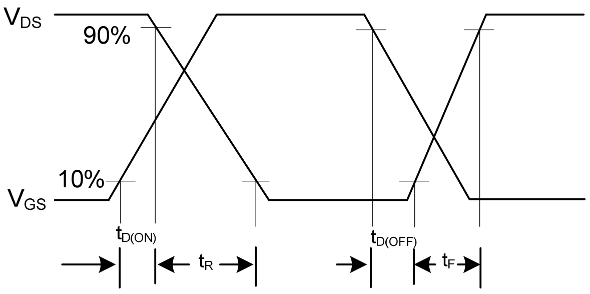


Peak Diode Recovery dv/dt Waveforms

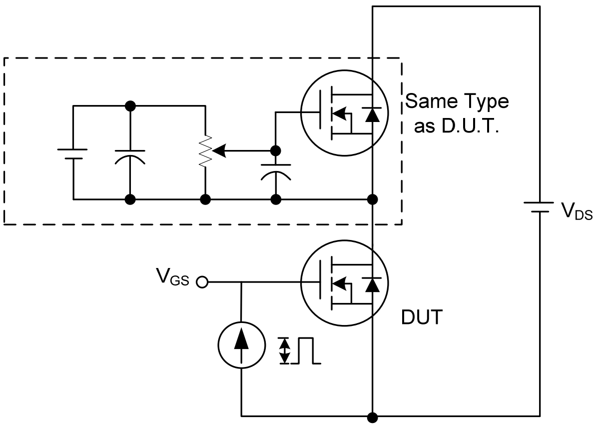
■ TEST CIRCUITS AND WAVEFORMS



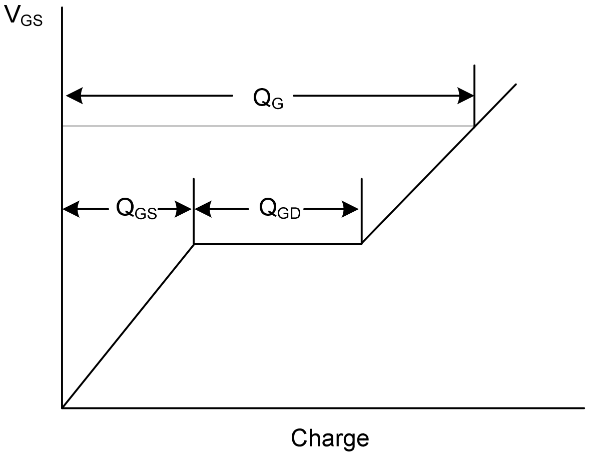
Switching Test Circuit



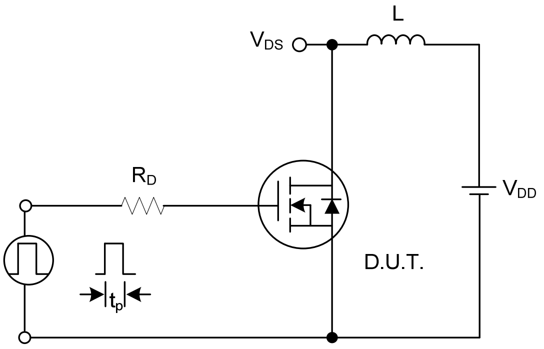
Switching Waveforms



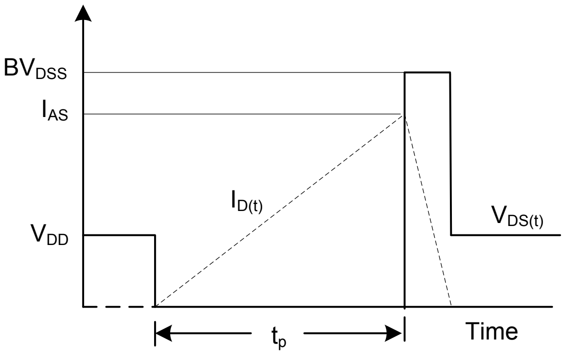
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms